

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	6	(laser near3 weld\$4 near9 polymer).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 09:40
L2	38	(laser near3 weld\$4 near9 plastic).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 09:52
L3	0	"425"/\$.ccor. and (laser near3 weld\$4).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 09:53
L4	10	((apparatus device) with plastic with laser near3 weld\$4).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 09:58
L5	32	((method process) with plastic with laser near3 weld\$4).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:28
L6	2	"20040104206"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 13:31
L7	2	6 and contamination same oxidation same resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:29
L8	18	(laser with (remov\$4 etch\$4)) same contamination same oxid\$7 same resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:38
L9	50	(laser with (remov\$4 etch\$4)) same contamination same oxid\$7 same (mask\$3 resist)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:39

## EAST Search History

L10	45	(laser with (remov\$4 etch\$4) with (mask\$3 resist)) same contamination same oxid\$7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:45
L11	29	10 not 8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:39
L12	2	11 and (laser with (remov\$4 etch\$4) with (semiconduct\$4 wafer silicon package ball grid array\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:43
L13	27	11 and (laser with (ball grid array\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:43
L14	0	11 and (laser with (bga (ball with (grid array\$3))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:44
L15	0	11 and (laser with (bga (ball grid)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:45
L16	0	11 and (bga (ball grid))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:45
L17	130	(laser with (remov\$4 etch\$4) with (mask\$3 resist) same (bga ball grid))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:46
L18	74	(laser with (remov\$4 etch\$4) with (mask\$3 resist) with (bga ball grid))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:47
L19	61	18 not 8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:55

## EAST Search History

L20	2	((mask\$3 resist) near3 (clean\$4 ablats\$4 remov\$4 etch\$4) with laser with (quick\$4 immediat\$4 rapid\$4)) same (mould\$4 mold\$4 automold\$4 automould\$4 encapsulat\$4 packag\$4 seal\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 10:59
L21	12	((mask\$3 resist) near3 (clean\$4 ablats\$4 remov\$4 etch\$4) with (quick\$4 immediat\$4 rapid\$4)) same (mould\$4 mold\$4 automold\$4 automould\$4 encapsulat\$4 packag\$4 seal\$4) same laser not 20	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 11:00
L22	49	((mask\$3 resist) near3 (clean\$4 ablats\$4 remov\$4 etch\$4) with (quick\$4 immediat\$4 rapid\$4) same laser) and (mould\$4 mold\$4 automold\$4 automould\$4 encapsulat\$4 packag\$4 seal\$4) not 20 not 21	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 11:01
L23	2	22 and (ball with (grid array))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 11:09
L24	1	("5950071").PN.	USPAT; USOCR	OR	OFF	2006/11/16 11:12
L25	1	24 and laser same rough\$7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 11:55
L26	54	(semiconductor with form\$4 with laser near3 etch\$3 with wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 11:56
L27	12	(semiconductor adj2 device with form\$4 with laser near3 etch\$3 with wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 11:56
L29	2	(("6031249") or ("6278132")).PN.	USPAT; USOCR	OR	OFF	2006/11/16 12:18
L30	2	L29 and semiconductor with insulating with silicon with wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 12:24

## EAST Search History

L37	4138	(resin plastic insulat\$4 glass ceramic dielectric) near3 substrate with (semiconductor die) near5 active	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 12:52
L38	882	37 and interpos\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 12:52
L39	264	(resin plastic insulat\$4 glass ceramic dielectric) near3 interpos\$4 with (semiconductor die) near5 active	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 12:53
L40	148	(resin plastic insulat\$4 glass ceramic dielectric) near3 interpos\$4 near3 (planar layer substrate) with (semiconductor die) near5 active	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 12:54
L41	2	(resin plastic insulat\$4 glass ceramic dielectric) near3 interposer near3 (planar layer substrate) with (semiconductor die) near5 active	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 12:56
L42	4	(resin plastic insulat\$4 glass ceramic dielectric) near3 interposer with (semiconductor die) near5 active	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 13:00
L43	4	42 and interposer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 12:58
L44	407	(resin plastic insulat\$4 glass ceramic dielectric) near3 interposer with (semiconductor die)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 13:00
L45	303	44 and interposer with (active contact electric\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 13:01
L46	21	44 and interposer with (active contact electric\$4) with opening	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 13:05

## EAST Search History

L47	5	44 and interposer with (active contact electric\$4) with opening and mold with interposer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 13:05
L48	1	6 and interposer same rough\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 13:32
L49	517	rough\$4 with surface with improv\$4 near3 bond\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 13:32
L50	434	rough\$4 near3 surface with improv\$4 near3 bond\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 13:33
L51	8	50 and rough\$4 with laser	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/16 13:33